



100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
100V	$22m\Omega$ @ $V_{GS} = 10V$	51.7A
	$30m\Omega$ @ $V_{GS} = 6V$	44.3A
	43.7mΩ @ V _{GS} = 4.5V	36.7A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

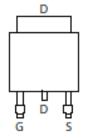
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH10H025LK3Q</u>)

Mechanical Data

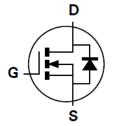
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🚯
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

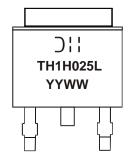
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H025LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



O'! = Manufacturer's Marking
TH1H025L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I _D	51.7 36.6	А
Pulsed Drain Current (10µs Pulse, T _C = +25°C, Package Limited)	I _{DM}	200	Α	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	77	Α
Pulsed Body Diode Forward Current (10µs Pulse, T _C = +25°C, Packa	I _{SM}	200	Α	
Avalanche Current, L = 0.1mH		I _{AS}	15.8	Α
Avalanche Energy, L = 0.1mH		E _{AS}	12.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	48	°C/W
Total Power Dissipation (Note 6)	P _D	100	W	
Thermal Resistance, Junction to Case (Note 6)		R _{0JC}	1.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	$V_{DS} = 80V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	•		•	•		•
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
		_	17.1	22	mΩ	$V_{GS} = 10V, I_D = 20A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	21.4	30		$V_{GS} = 6V, I_D = 20A$
	, ,	_	28.3	43.7		$V_{GS} = 4.5V, I_D = 20A$
Diode Forward Voltage	V_{SD}	_	_	1.3	V	$V_{GS} = 0V, I_S = 20A$
DYNAMIC CHARACTERISTICS (Note 8)						•
Input Capacitance	C _{iss}	1	1477	_		V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	Coss	_	263	_	pF	
Reverse Transfer Capacitance	Crss	_	20	_		
Gate Resistance	R_{G}	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q_{G}	_	21	_		
Gate-Source Charge	Q _{GS}	_	5.7	_	nC	$V_{DD} = 50V, I_D = 20A,$ $V_{GS} = 10V$
Gate-Drain Charge	Q_{GD}	_	3.8	_		
Turn-On Delay Time	t _{D(ON)}	_	6.3	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 6\Omega$
Turn-On Rise Time	t _R		9.4	_		
Turn-Off Delay Time	t _{D(OFF)}	_	16.7	_	ns	
Turn-Off Fall Time	t _F		8.2	_		
Reverse Recovery Time	t _{RR}		38.7	_	ns	1 004 11/14 4004/
Reverse Recovery Charge	Q _{RR}		53.7	_	nC	I _F = 20A, di/dt = 100A/μs

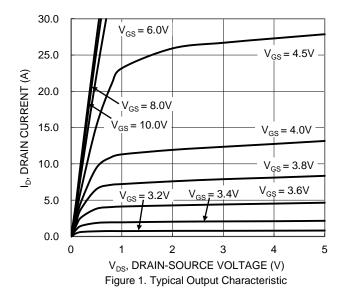
lotes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

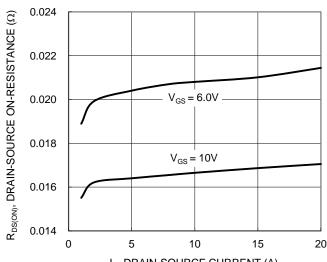
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

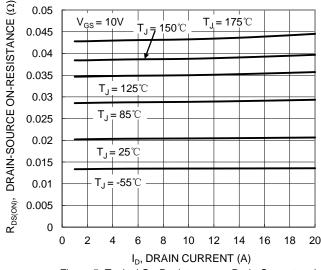


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

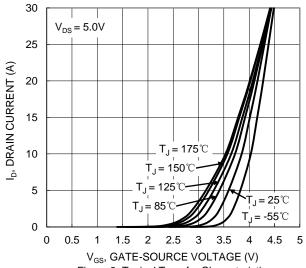


Figure 2. Typical Transfer Characteristic

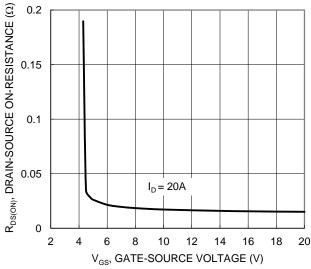


Figure 4. Typical Transfer Characteristic

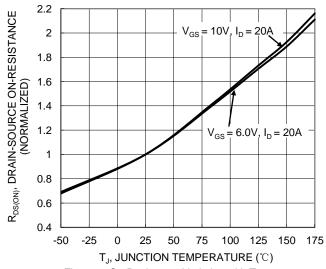


Figure 6. On-Resistance Variation with Temperature



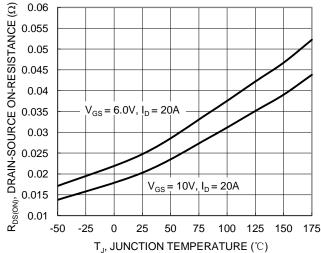


Figure 7. On-Resistance Variation with Temperature

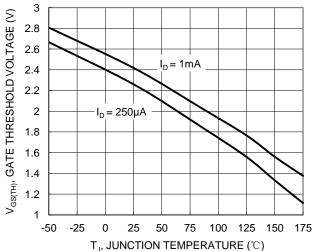


Figure 8. Gate Threshold Variation vs. Junction Temperature

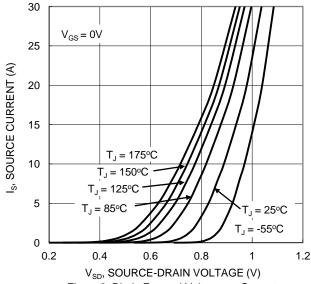
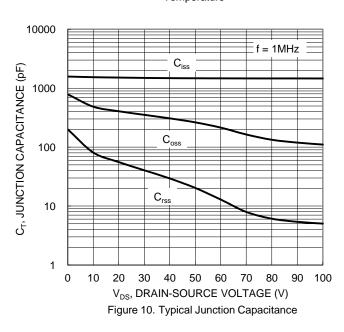
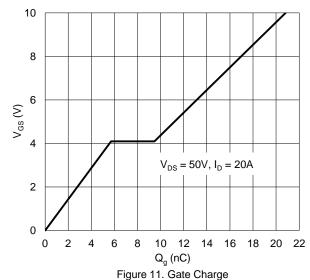


Figure 9. Diode Forward Voltage vs. Current





100 $= 10 \mu s$ DRAIN CURRENT (A) 10 1 = 1ms T_{J(Max)} = 175 ℃ -----= 10ms T_C = 25°C ۵_ Single Pulse 0.1 $P_W = 100 \dot{m} s$ **DUT** on Infinite Heatsink $V_{GS} = 10V$ 0.01 10 100 0.1 1000 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

1000



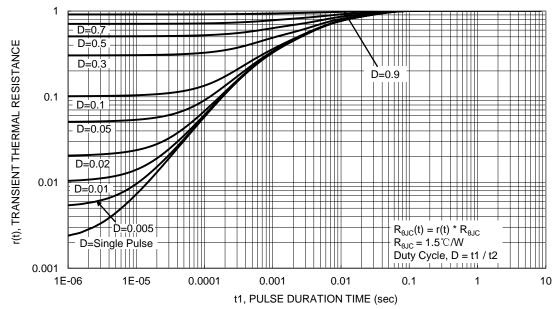


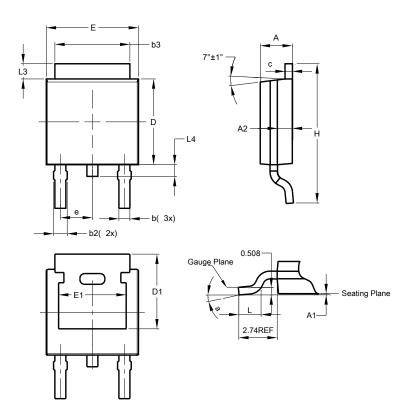
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

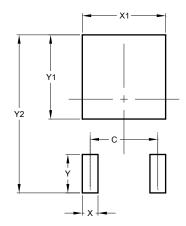


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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